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Kind regards,

Team Nexperia



# PSMN025-100D

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 4 — 12 January 2012

Product data sheet

## 1. Product profile

### 1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC converters
- Switched-mode power supplies

### 1.4 Quick reference data

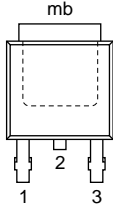
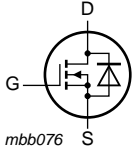
Table 1. Quick reference data

| Symbol                         | Parameter                        | Conditions  | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|-----|-----|-----|------|
| $V_{DS}$                       | drain-source voltage             | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$   | -   | -   | 100 | V    |
| $I_D$                          | drain current                    | $T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a> ;<br>see <a href="#">Figure 4</a>                   | -   | -   | 47  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>   | -   | -   | 150 | W    |
| <b>Static characteristics</b>  |                                  |   |     |     |     |      |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$<br>see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a> | -   | 22  | 25  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |   |     |     |     |      |
| $Q_{GD}$                       | gate-drain charge                | $V_{GS} = 10\text{ V}; I_D = 45\text{ A}; V_{DS} = 80\text{ V};$<br>$T_j = 25\text{ °C};$ see <a href="#">Figure 13</a>         | -   | 25  | -   | nC   |



## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline  | Graphic symbol  |
|-----|--------|-----------------------------------|---|---|
| 1   | G      | gate                              |  |  |
| 2   | D      | drain <sup>[1]</sup>              |   |   |
| 3   | S      | source                            |   |   |
| mb  | D      | mounting base; connected to drain |   |   |

**SOT428 (DPAK)**

[1] It is not possible to make connection to pin 2.

## 3. Ordering information

Table 3. Ordering information

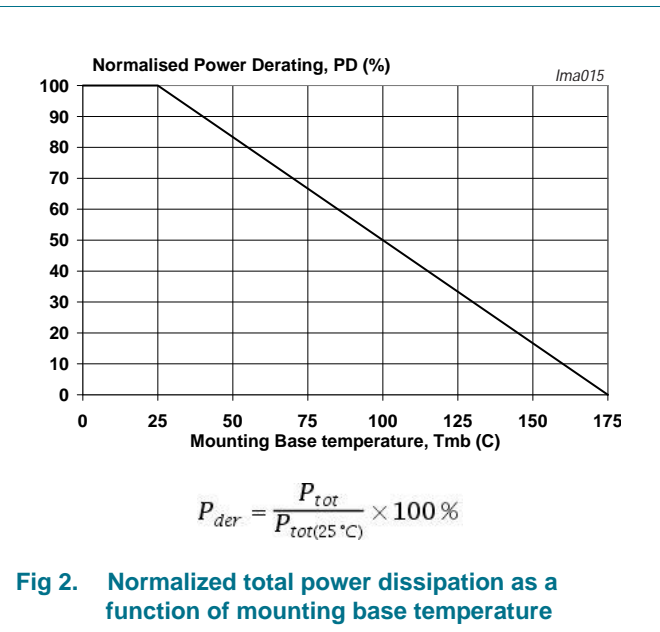
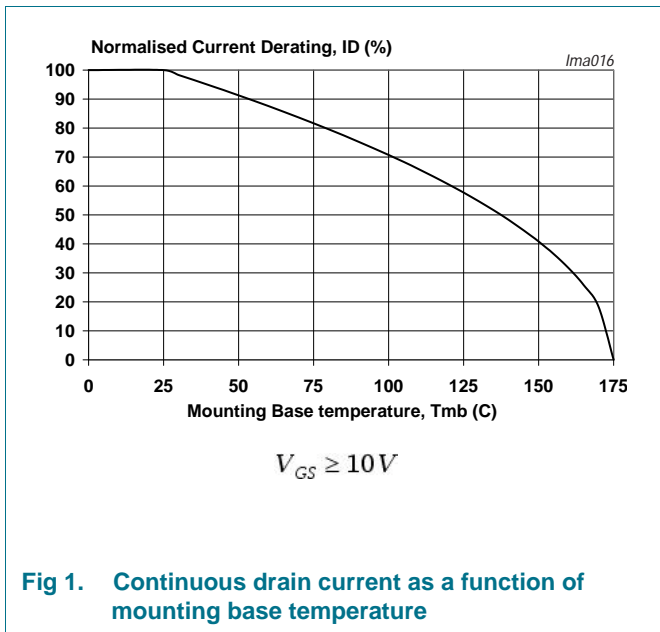
| Type number  | Package |   | Version |
|--------------|---------|---|---------|
|              | Name    | Description   |         |
| PSMN025-100D | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

### 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions  | Min | Max | Unit |
|-----------------------------|--|---|-----|-----|------|
| V <sub>DS</sub>             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C   | -   | 100 | V    |
| V <sub>DGR</sub>            | drain-gate voltage                           | T <sub>j</sub> ≤ 175 °C; T <sub>j</sub> ≥ 25 °C; R <sub>GS</sub> = 20 kΩ  | -   | 100 | V    |
| V <sub>GS</sub>             | gate-source voltage                          |   | -20 | 20  | V    |
| I <sub>D</sub>              | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a>  | -   | 33  | A    |
|                             |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a> ; see <a href="#">Figure 4</a>  | -   | 47  | A    |
| I <sub>DM</sub>             | peak drain current                           | pulsed; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 4</a>   | -   | 188 | A    |
| P <sub>tot</sub>            | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>   | -   | 150 | W    |
| T <sub>stg</sub>            | storage temperature                          |   | -55 | 175 | °C   |
| T <sub>j</sub>              | junction temperature                         |   | -55 | 175 | °C   |
| <b>Source-drain diode</b>   |  |   |     |     |      |
| I <sub>S</sub>              | source current                               | T <sub>mb</sub> = 25 °C   | -   | 47  | A    |
| I <sub>SM</sub>             | peak source current                          | pulsed; T <sub>mb</sub> = 25 °C   | -   | 188 | A    |
| <b>Avalanche ruggedness</b> |  |   |     |     |      |
| E <sub>DS(AL)S</sub>        | non-repetitive drain-source avalanche energy | V <sub>GS</sub> = 10 V; T <sub>j(initial)</sub> = 25 °C; I <sub>D</sub> = 40 A; V <sub>sup</sub> ≤ 25 V; unclamped; t <sub>p</sub> = 100 μs; R <sub>GS</sub> = 50 Ω | -   | 260 | mJ   |
| I <sub>AS</sub>             | non-repetitive avalanche current             | V <sub>sup</sub> ≤ 25 V; V <sub>GS</sub> = 10 V; T <sub>j(initial)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω; unclamped; see <a href="#">Figure 3</a>                   | -   | 47  | A    |



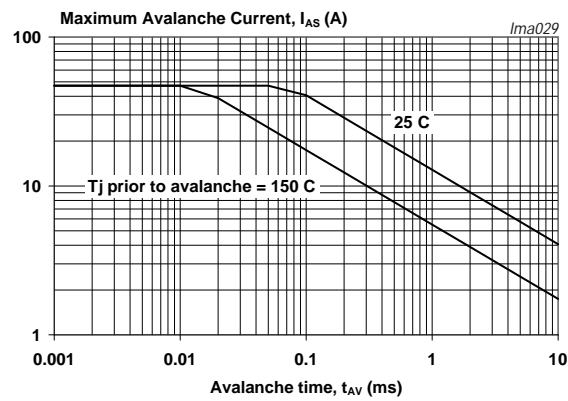


Fig 3. Maximum permissible non-repetitive avalanche current as a function of avalanche time

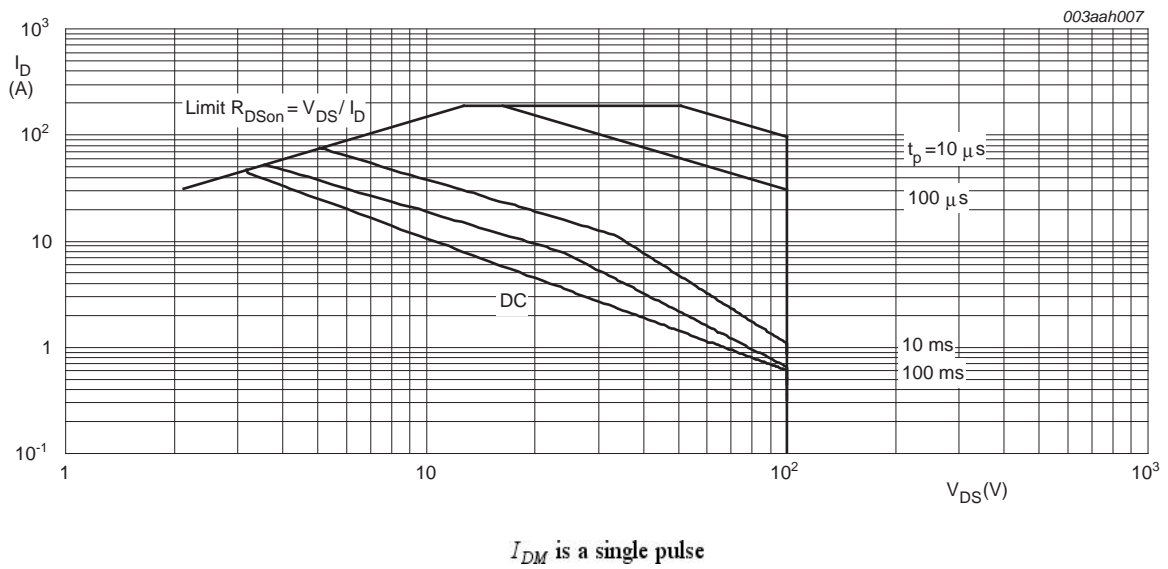
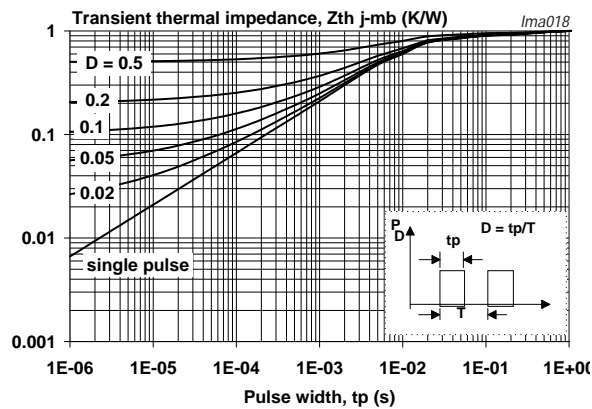


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol         | Parameter   | Conditions   | Min | Typ | Max | Unit |
|----------------|---|--|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <a href="#">Figure 5</a>                                       | -   | -   | 1   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | SOT428 package ; printed-circuit board mounted ; minimum footprint | -   | 50  | -   | K/W  |



**Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                        | Conditions  | Min | Typ  | Max | Unit          |
|--------------------------------|----------------------------------|---|-----|------|-----|---------------|
| <b>Static characteristics</b>  |                                  |   |     |      |     |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$   | 89  | -    | -   | V             |
|                                |                                  | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | 100 | -    | -   | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage    | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 9</a>  | 1   | -    | -   | V             |
|                                |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>           | 2   | 3    | 4   | V             |
|                                |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 9</a>  | -   | -    | 6   | V             |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$   | -   | 0.05 | 10  | $\mu\text{A}$ |
|                                |                                  | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$  | -   | -    | 500 | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -   | 0.02 | 100 | nA            |
|                                |                                  | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$   | -   | 0.02 | 100 | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 11</a>                                   | -   | -    | 68  | m $\Omega$    |
|                                |                                  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>    | -   | 22   | 25  | m $\Omega$    |
| <b>Dynamic characteristics</b> |                                  |   |     |      |     |               |
| $Q_{G(tot)}$                   | total gate charge                | $I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$<br>$T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>           | -   | 61   | -   | nC            |
| $Q_{GS}$                       | gate-source charge               |   | -   | 13   | -   | nC            |
| $Q_{GD}$                       | gate-drain charge                |   | -   | 25   | -   | nC            |
| $C_{iss}$                      | input capacitance                | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 14</a>             | -   | 2600 | -   | pF            |
| $C_{oss}$                      | output capacitance               |   | -   | 340  | -   | pF            |
| $C_{riss}$                     | reverse transfer capacitance     |   | -   | 195  | -   | pF            |
| $t_{d(on)}$                    | turn-on delay time               | $V_{DS} = 50 \text{ V}; R_L = 1.8 \text{ } \Omega; V_{GS} = 10 \text{ V};$<br>$R_{G(ext)} = 5.6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$ | -   | 18   | -   | ns            |
| $t_r$                          | rise time                        |   | -   | 72   | -   | ns            |
| $t_{d(off)}$                   | turn-off delay time              |   | -   | 69   | -   | ns            |
| $t_f$                          | fall time                        |   | -   | 58   | -   | ns            |
| $L_D$                          | internal drain inductance        | measured from tab to centre of die ;<br>$T_j = 25 \text{ }^\circ\text{C}$   | -   | 3.5  | -   | nH            |
| $L_S$                          | internal source inductance       | measured from source lead to source<br>bond pad ; $T_j = 25 \text{ }^\circ\text{C}$   | -   | 7.5  | -   | nH            |
| <b>Source-drain diode</b>      |                                  |   |     |      |     |               |
| $V_{SD}$                       | source-drain voltage             | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 15</a>                                     | -   | 0.87 | 1.2 | V             |
| $t_{rr}$                       | reverse recovery time            | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$<br>$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$     | -   | 82   | -   | ns            |
| $Q_r$                          | recovered charge                 |   | -   | 0.26 | -   | $\mu\text{C}$ |

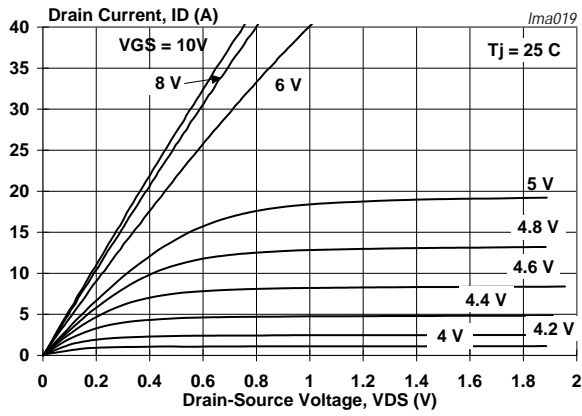


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical function of drain-source voltage; typical values

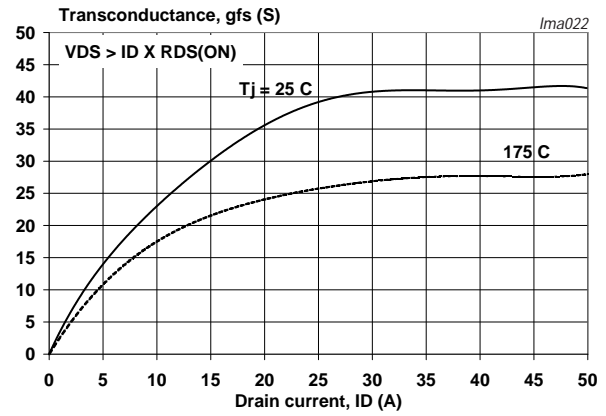


Fig 7. Forward transconductance as a function of drain current; typical values

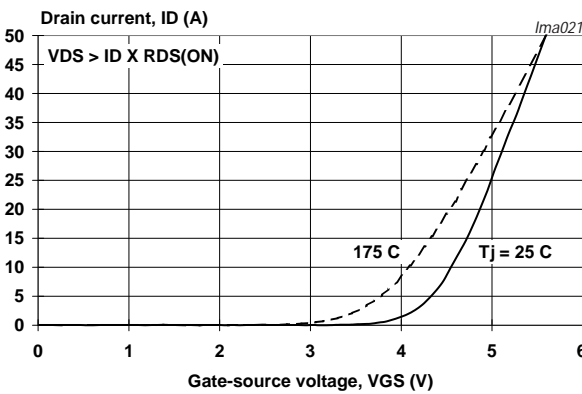


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

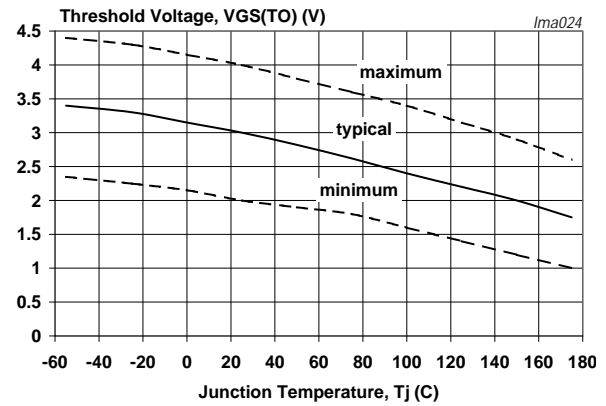


Fig 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$



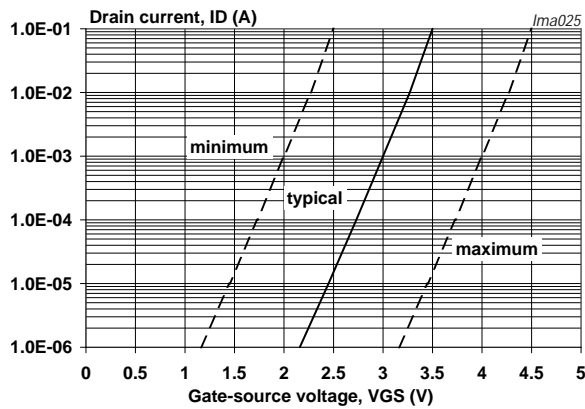


Fig 10. Sub-threshold drain current as a function of gate-source voltage

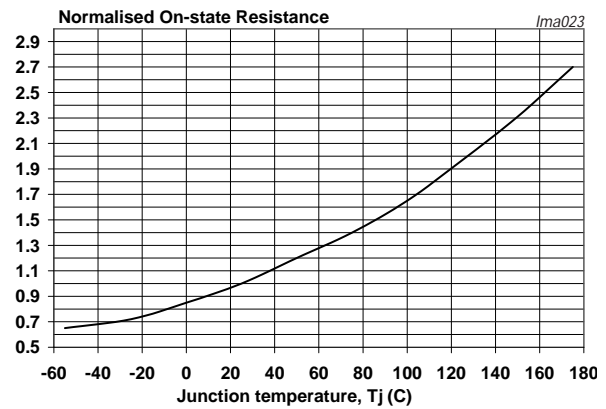


Fig 11. Normalized drain source on-state resistance factor as a function of junction temperature

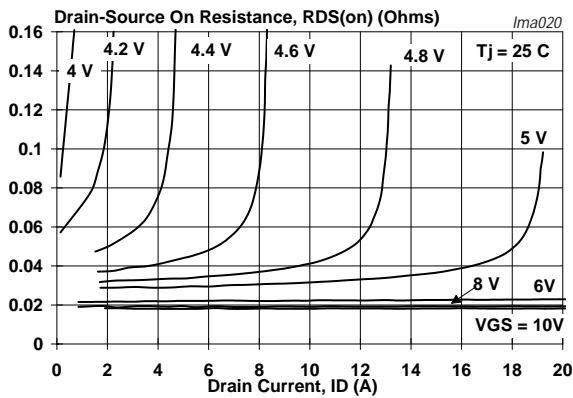


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

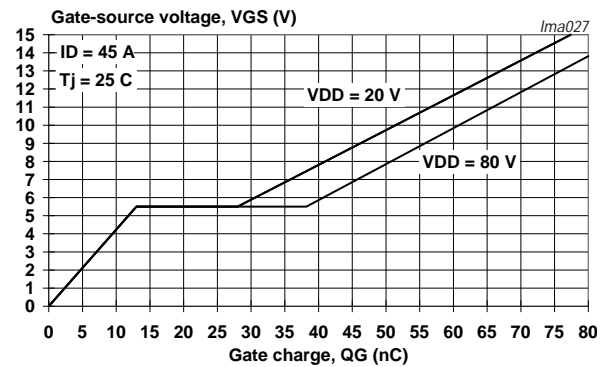


Fig 13. Gate-source voltage as a function of gate charge; typical values

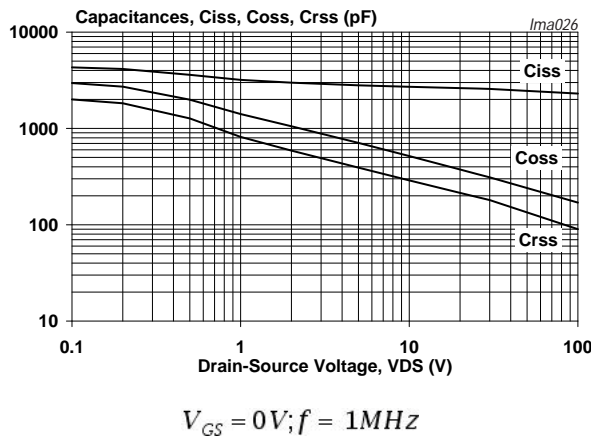


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

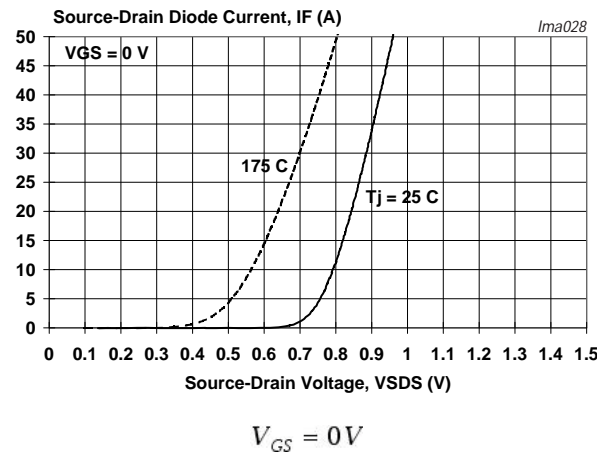


Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

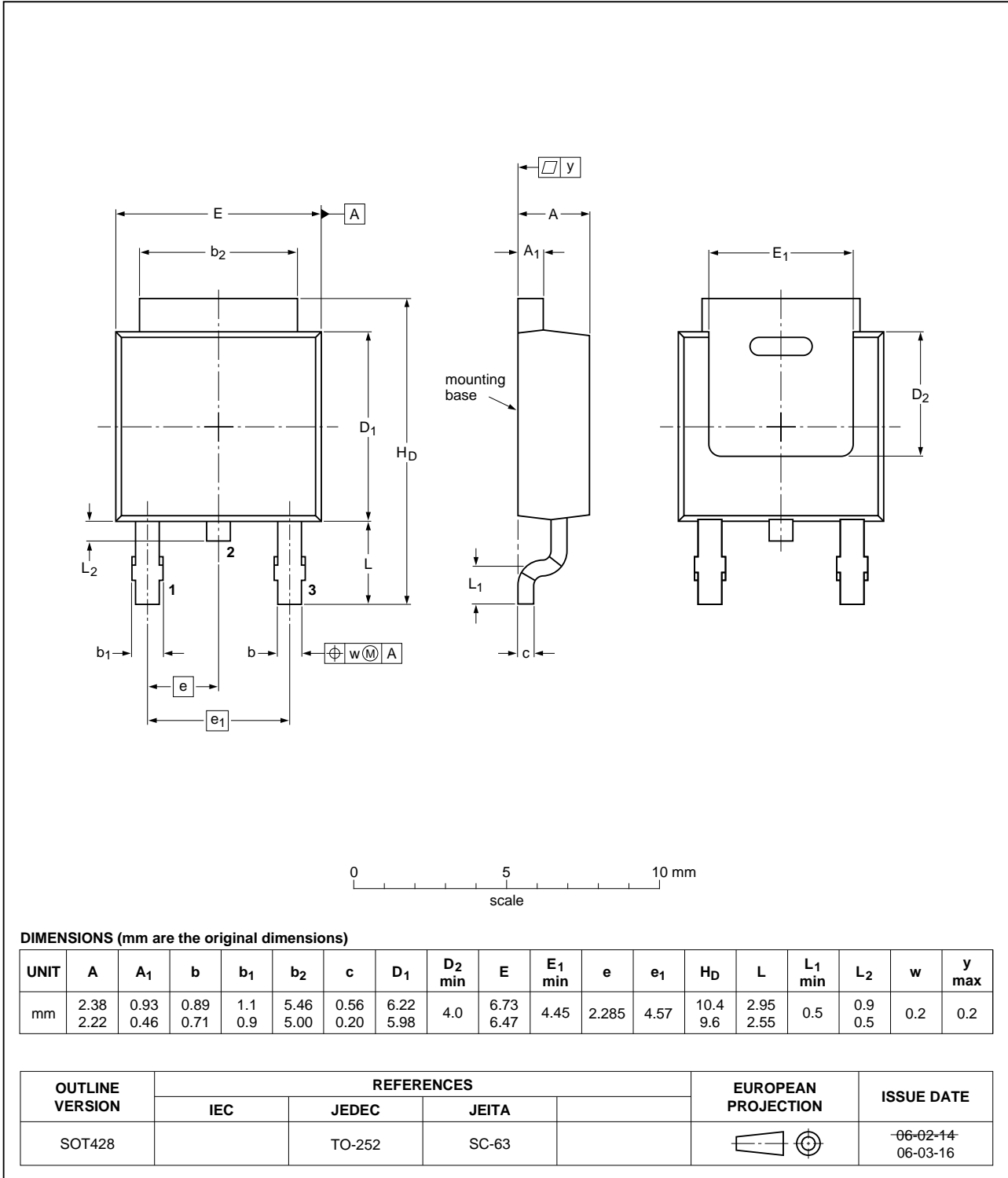


Fig 16. Package outline SOT428 (DPAK)

## 8. Revision history

Table 7. Revision history

| Document ID      | Release date                  | Data sheet status  | Change notice | Supersedes       |
|------------------|-------------------------------|--------------------|---------------|------------------|
| PSMN025-100D v.4 | 20120112                      | Product data sheet | -             | PSMN025-100D v.3 |
| Modifications:   | • Various changes to content. |                    |               |                  |
| PSMN025-100D v.3 | 20081120                      | Product data sheet | -             | PSMN025-100D v.2 |

## 9. Legal information

### 9.1 Data sheet status

| Document status <a href="#">[1]</a> <a href="#">[2]</a> | Product status <a href="#">[3]</a> | Definition  |
|---|------------------------------------|---|
| Objective [short] data sheet                            | Development                        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet                          | Qualification                      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet                              | Production                         | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 11. Contents

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|           |  |           |
|-----------|--|-----------|
| <b>1</b>  | <b>Product profile</b> . . . . .         | <b>1</b>  |
| 1.1       | General description . . . . .            | 1         |
| 1.2       | Features and benefits . . . . .          | 1         |
| 1.3       | Applications . . . . .                   | 1         |
| 1.4       | Quick reference data . . . . .           | 1         |
| <b>2</b>  | <b>Pinning information</b> . . . . .     | <b>2</b>  |
| <b>3</b>  | <b>Ordering information</b> . . . . .    | <b>2</b>  |
| <b>4</b>  | <b>Limiting values</b> . . . . .         | <b>3</b>  |
| <b>5</b>  | <b>Thermal characteristics</b> . . . . . | <b>5</b>  |
| <b>6</b>  | <b>Characteristics</b> . . . . .         | <b>6</b>  |
| <b>7</b>  | <b>Package outline</b> . . . . .         | <b>10</b> |
| <b>8</b>  | <b>Revision history</b> . . . . .        | <b>11</b> |
| <b>9</b>  | <b>Legal information</b> . . . . .       | <b>12</b> |
| 9.1       | Data sheet status . . . . .              | 12        |
| 9.2       | Definitions . . . . .                    | 12        |
| 9.3       | Disclaimers . . . . .                    | 12        |
| 9.4       | Trademarks . . . . .                     | 13        |
| <b>10</b> | <b>Contact information</b> . . . . .     | <b>13</b> |

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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